

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology
- ★ 100% EAS Guaranteed

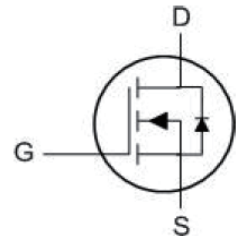
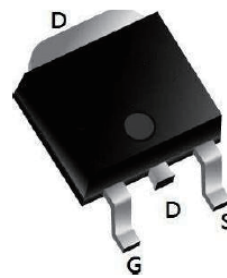
Product Summary

BVDSS	RDS(on)	ID
30V	3.5mΩ	100A

Description

The 100N03 is the high cell density trenched N-ch MOSFETs, which provide excellent RDS(on) and gate charge for most of the synchronous buck converter applications.

The 100N03 meet the RoHS and Green Product, requirement 100% EAS guaranteed with full function reliability approved.

TO252 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units	
V_{DSS}	Drain-Source Voltage	30	V	
V_{GSS}	Gate-Source Voltage	±20	V	
I_D	Continuous Drain Current	TC = 25°C	100	A
		TC = 100°C	65	A
I_{DM}	Pulsed Drain Current ^{note1}	400	A	
E_{AS}	Single Pulsed Avalanche Energy ^{note2}	95	mJ	
P_D	Power Dissipation	TC = 25°C	80	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.9	°C/W	
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	°C	

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V,$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\ \mu\text{A}$	1	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	$V_{GS}=10V, I_D=30A$	-	3.5	4.7	m Ω
		$V_{GS}=4.5V, I_D=20A$	-	5.5	10	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1.0\text{MHz}$	-	2100	-	pF
C_{oss}	Output Capacitance		-	326	-	
C_{rss}	Reverse Transfer Capacitance		-	282	-	
Q_g	Total Gate Charge	$V_{DS}=15V, I_D=30A, V_{GS}=10V$	-	45	-	nC
Q_{gs}	Gate-Source Charge		-	3	-	
Q_{gd}	Gate-Drain("Miller") Charge		-	15	-	
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15V, I_D=30A, R_{GEN}=3\ \Omega,$ $V_{GS}=10V$	-	21	-	ns
t_r	Turn-on Rise Time		-	32	-	
$t_{d(off)}$	Turn-off Delay Time		-	59	-	
t_f	Turn-off Fall Time		-	34	-	
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	50	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	200	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=30A$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20A, di/dt=100A/\ \mu\text{s}$	-	15	-	ns
Q_{rr}	Body Diode Reverse Recovery Time Charge		-	4	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: $T_J=25^\circ\text{C}, V_G=10V, R_G=25\ \Omega, L=0.5\text{mH}, I_{AS}=18.4A$
3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 0.5\%$



Typical Electrical and Thermal Characteristics (Curves)

Figure 1: Output Characteristics

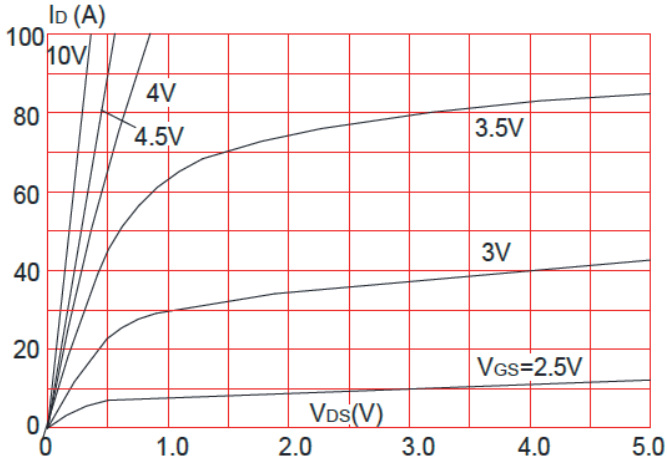


Figure 2: Typical Transfer Characteristics

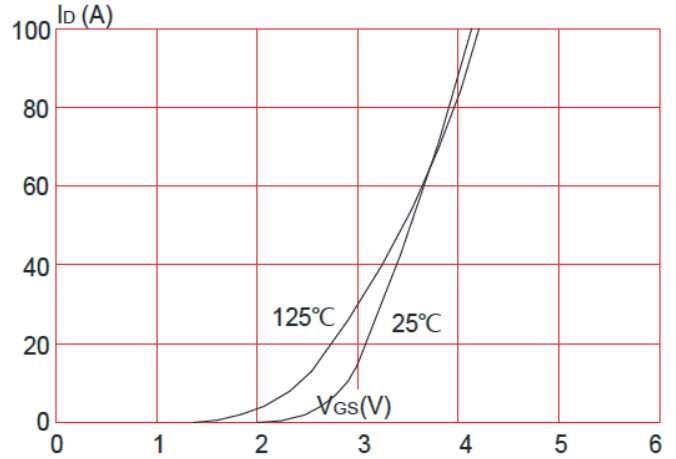


Figure 3: On-resistance vs. Drain Current

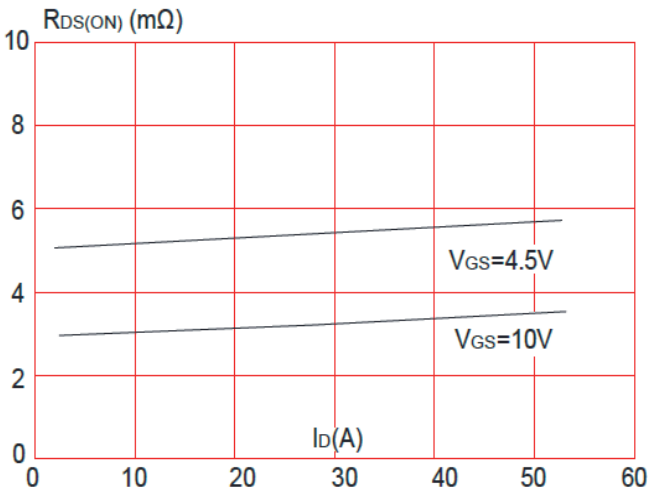


Figure 4: Body Diode Characteristics

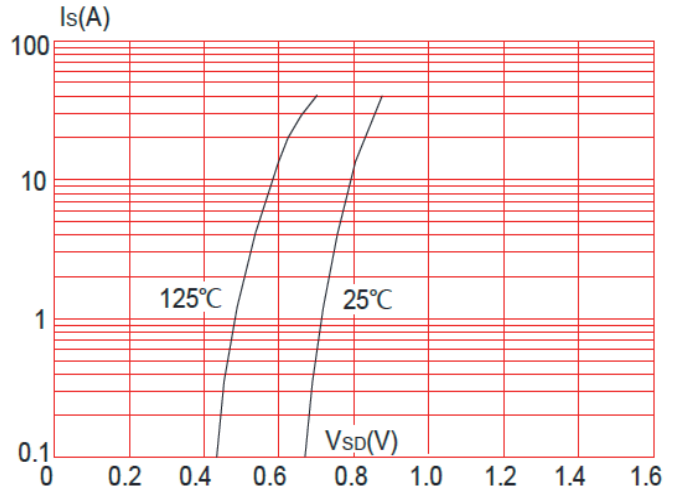


Figure 5: Gate Charge Characteristics

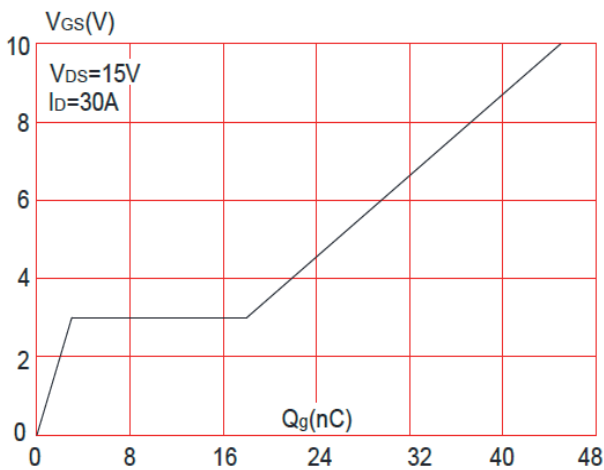
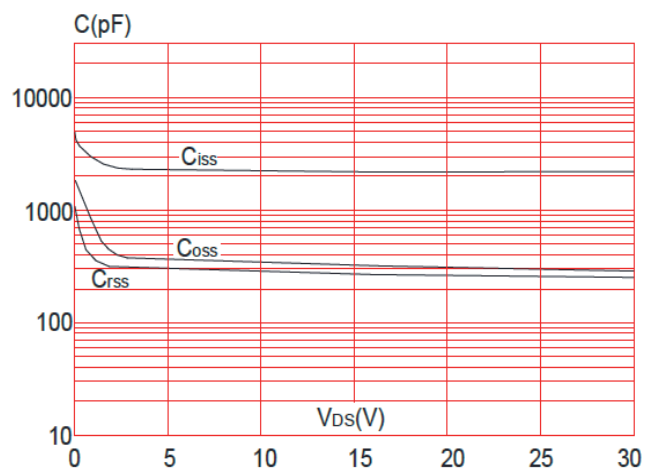


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

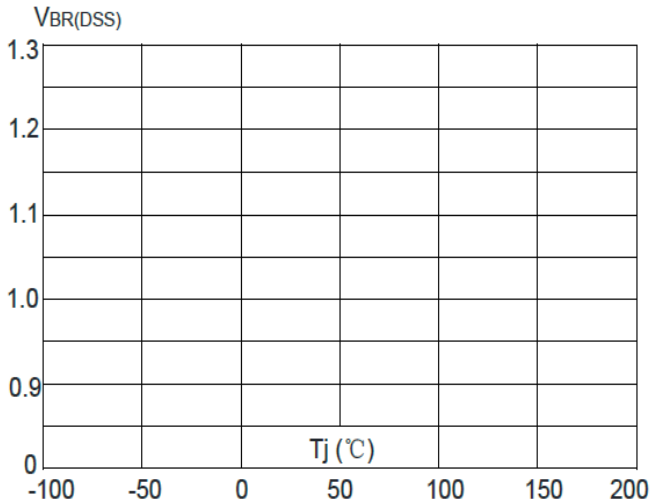


Figure 8: Normalized on Resistance vs. Junction Temperature

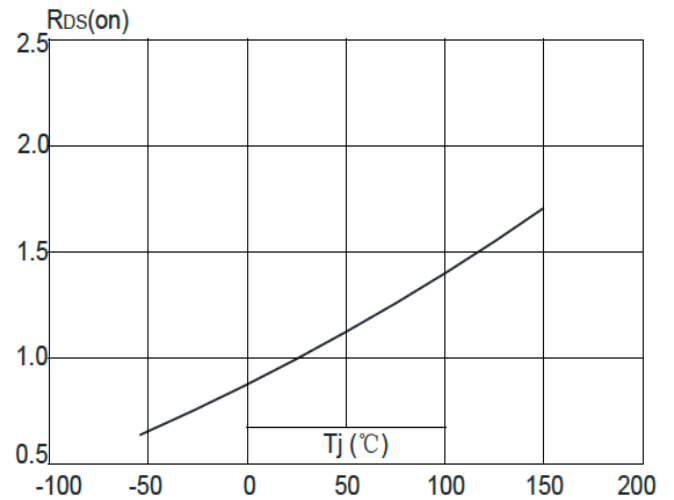


Figure 9: Maximum Safe Operating Area

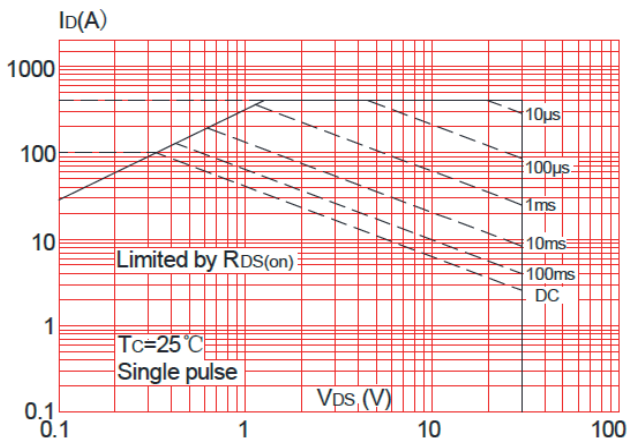


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

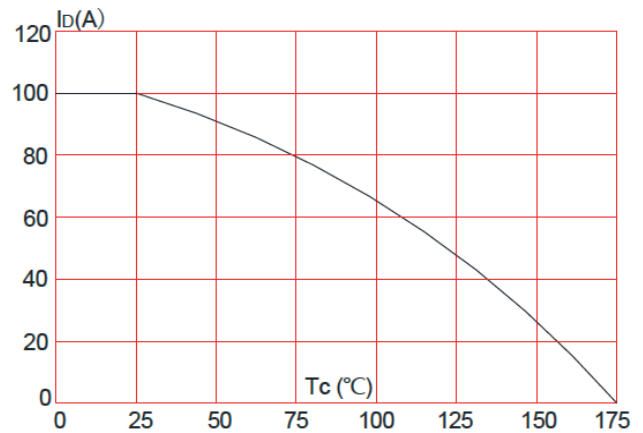
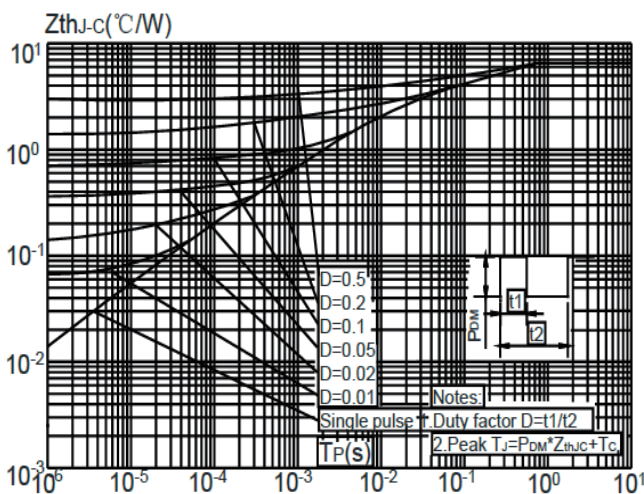


Figure 11: Maximum Effective Transient Thermal Impedance vs. Junction Temperature



Test Circuit

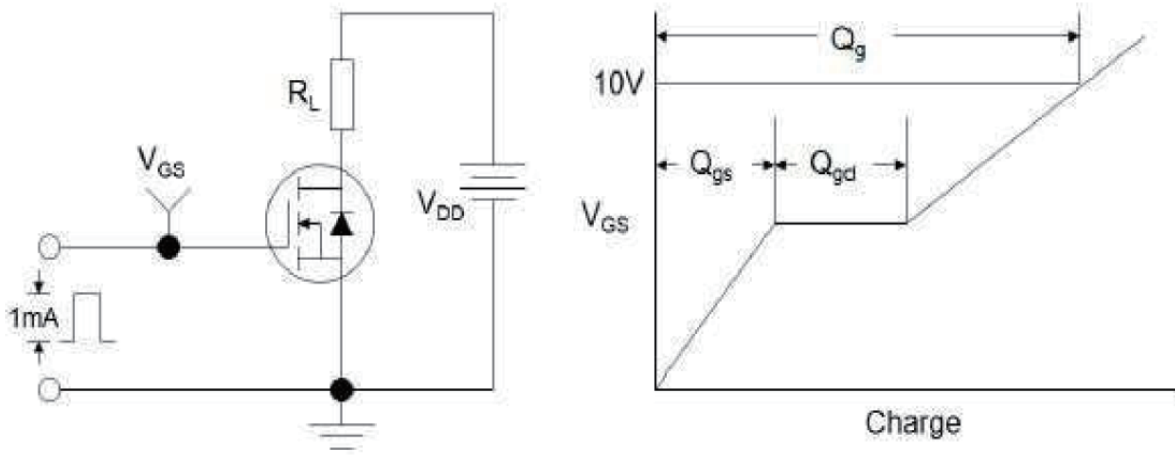


Figure1:Gate Charge Test Circuit & Waveform

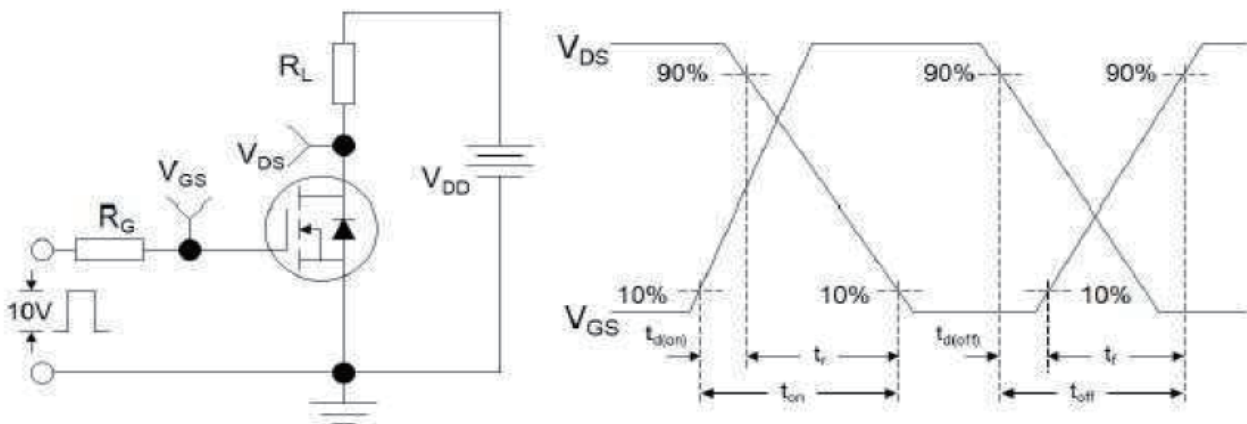


Figure 2: Resistive Switching Test Circuit & Waveforms

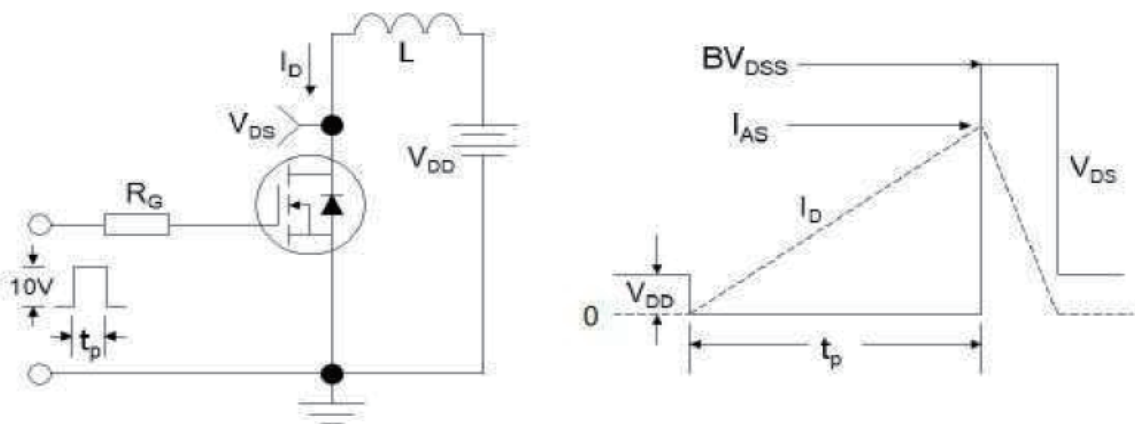
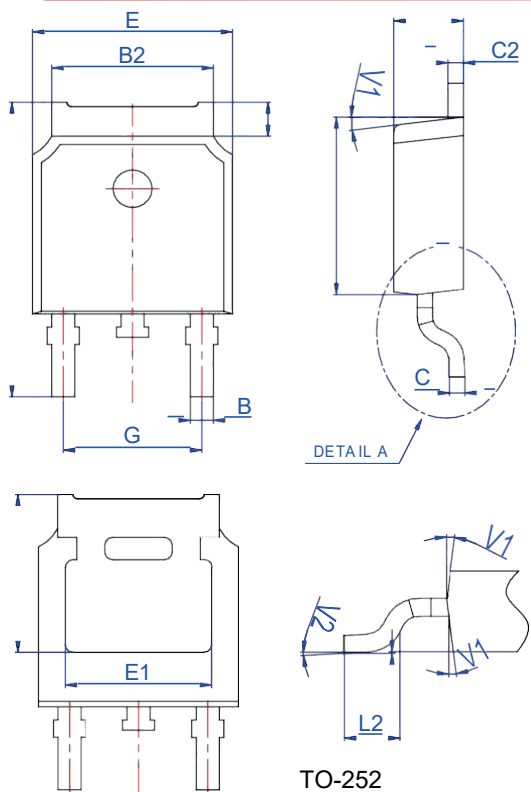


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

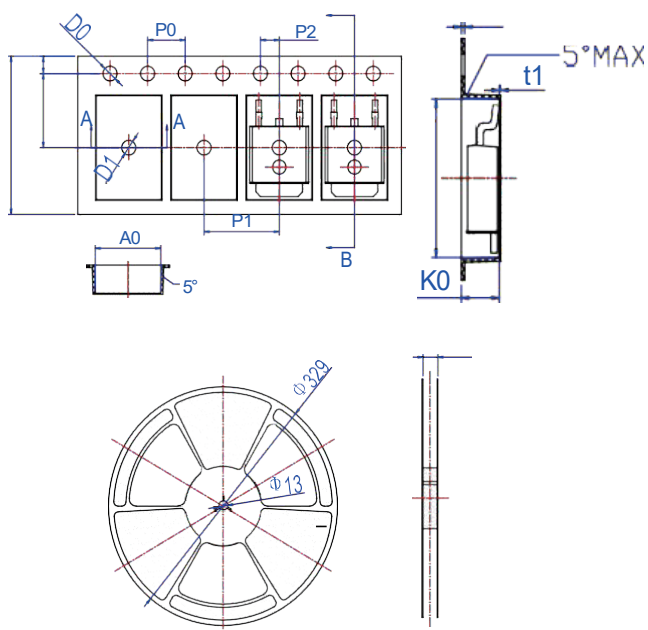
Package Mechanical Data-TO-252-4R



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.1		2.5	0.083		0.098
A2	0		0.1	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.4		0.6	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.9		6.3	0.232		0.248
D1	5.30REF			0.209REF		
E	6.4		6.8	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.5		10.7	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.9	16	16.1	0.626	0.63	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.4	7.5	7.6	0.291	0.295	0.299
D0	1.4	1.5	1.6	0.055	0.059	0.063
D1	1.4	1.5	1.6	0.055	0.059	0.063
P0	3.9	4	4.1	0.154	0.157	0.161
P1	7.9	8	8.1	0.311	0.315	0.319
P2	1.9	2	2.1	0.075	0.079	0.083
A0	6.85	6.9	7	0.27	0.271	0.276
B0	10.45	10.5	10.6	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.1			0.004		
10P0	39.8	40	40.2	1.567	1.575	1.583

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